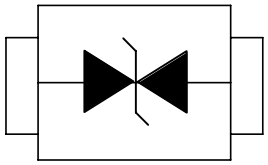
FEATURES

- Bi-directional ESD protection of one line
- Low capacitance: 12pF(Typ.)
- Low reverse stand−off voltage: 5.0V
- Low reverse clamping voltage
- Low leakage current
- Fast response time
- JESD22-A114-B ESD Rating of class 3B per human body model
- IEC 61000-4-2 Level 4 ESD protection

SOD-323



Pin Configuration

APPLICATIONS

- Computers and peripherals
- PAD
- Audio and video equipment
- Cellular handsets and accessories
- Subscriber identity module(SIM) card protection
- Portable electronics
- Other electronics equipments communi-cation systems

MAXIMUM RATINGS (T_a =25℃ unless otherwise noted)

Parameter		Symbol	Limit	Unit
IEC 61000-4-2 ESD Voltage	Air Model	V_{ESD} (1)	±25	kV
	Contact Model		±25	
JESD22-A114-B ESD Voltage	Per Human Body Model		±16	
ESD Voltage	Machine Model		±0.4	
Peak Pulse Power		P_{PP} (2)	120	W
Peak Pulse Current		I_{PP} (2)	5	A
Lead Solder Temperature − Maximum (10 Second Duration)		T_L	260	℃
Junction Temperature		T_j	150	℃
Storage Temperature Range		T_{stg}	-55 ~ +150	℃

(1).Device stressed with ten non-repetitive ESD pulses.

(2).Non-repetitive current pulse 8/20μs exponential decay waveform according to IEC61000-4-5.

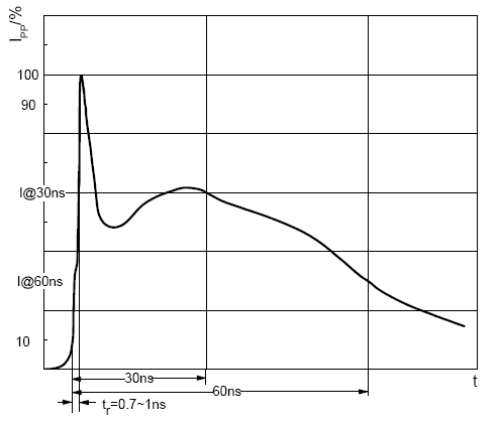
ESD standards compliance

IEC61000-4-2 Standard

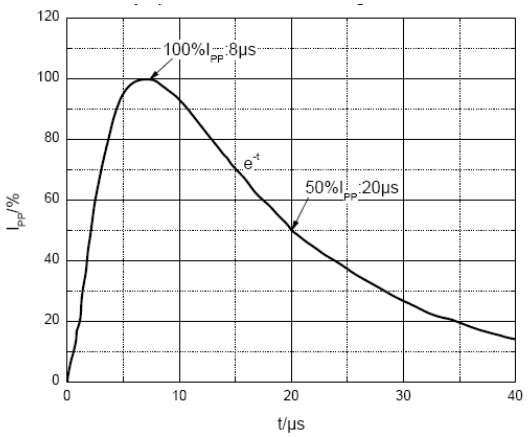
Contact Discharge		Air Discharge	
Level	Test Voltage kV	Level	Test Voltage kV
1	2	1	2
2	4	2	4
3	6	3	8
4	8	4	15

JESD22-A114-B Standard

ESD Class	Human Body Discharge V
0	0～249
1A 1B 1C	250～499 500～999 1000～1999
2	2000～3999
3A 3B	4000～7999 8000～15999



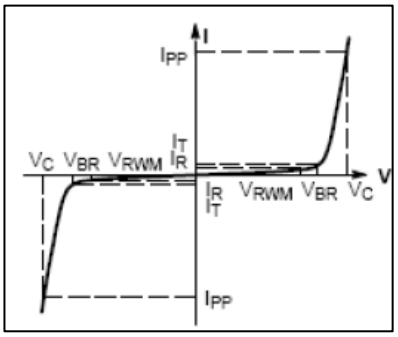
ESD pulse waveform according to IEC61000-4-2



8/20μs pulse waveform according to IEC 61000-4-5

ELECTRICAL PARAMETER

Symbol	Parameter
V_C	Clamping Voltage @ I_{PP}
I_{PP}	Peak Pulse Current
V_{BR}	Breakdown Voltage @ I_T
I_T	Test Current
I_R	Reverse Leakage Current @ V_{RWM}
V_{RWM}	Reverse Standoff Voltage



V-I characteristics for a Bi-directional TVS

ELECTRICAL CHARACTERISTICS(T_a=25℃ unless otherwise specified)

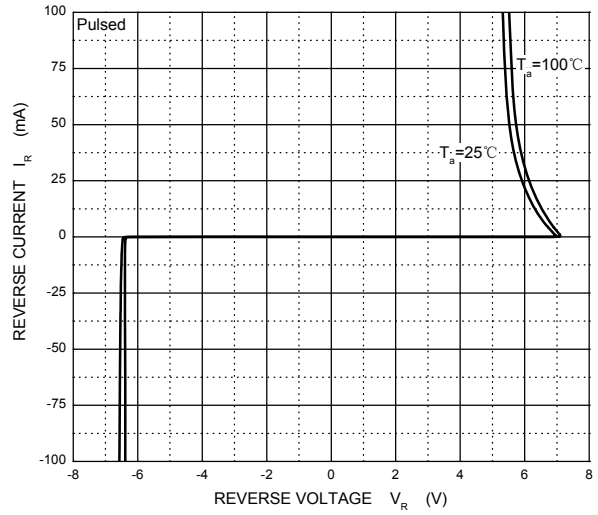
Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Reverse stand off voltage	V_{RWM} (1)				5	V
Reverse leakage current	I_R	V_{RWM}=5V			0.1	μA
Breakdown voltage	$V_{(BR)}$	I_T=1mA	5.8		8.3	V
Clamping voltage	V_C (2)	I_{PP}=5A			10	V
Junction capacitance	C_J	V_R=0V,f=1MHz		12	15	pF

(1).Other voltages available upon request.

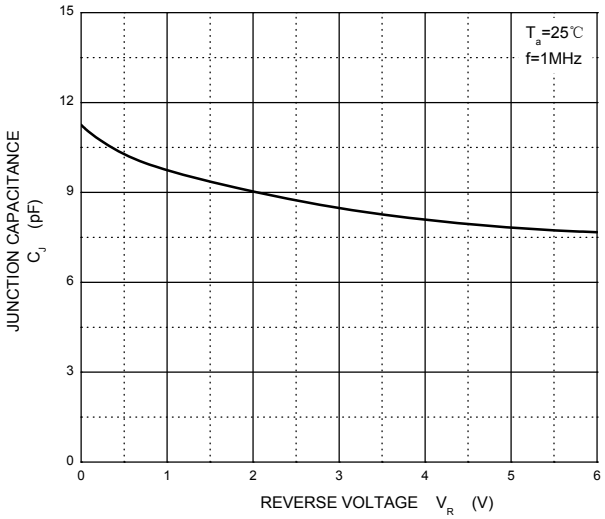
(2).Non-repetitive current pulse 8/20μs exponential decay waveform according to IEC61000-4-5

TYPICAL CHARACTERISTICS

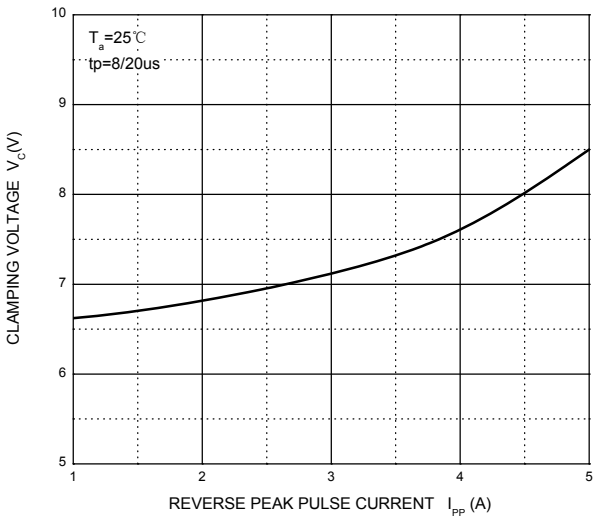
Reverse Characteristics



Capacitance Characteristics

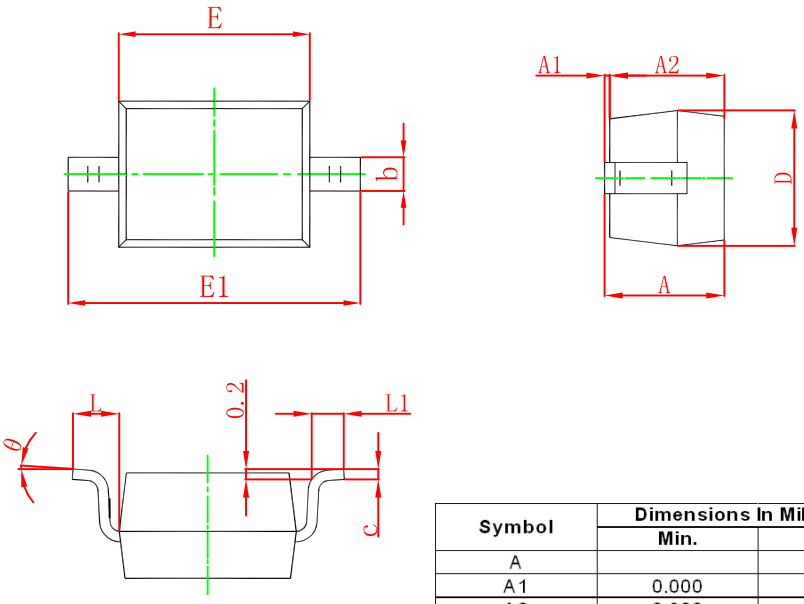


V_C —— I_{PP}



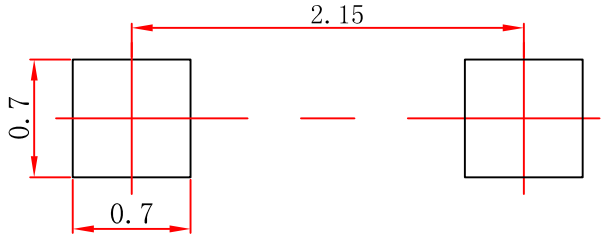
PACKAGE OUTLINEAND PAD LAYOUT INFORMATION

SOD-323 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A		1.000		0.039
A1	0.000	0.100	0.000	0.004
A2	0.800	0.900	0.031	0.035
b	0.250	0.350	0.010	0.014
c	0.080	0.150	0.003	0.006
D	1.200	1.400	0.047	0.055
E	1.600	1.800	0.063	0.071
E1	2.550	2.750	0.100	0.108
L	0.475 REF.		0.019 REF.	
L1	0.250	0.400	0.010	0.016
θ	0°	8°	0°	8°

SOD-323 Suggested Pad Layout



Note:
1.Controlling dimension:in millimeters.
2.General tolerance:±0.05mm.
3.The pad layout is for reference purposes only.